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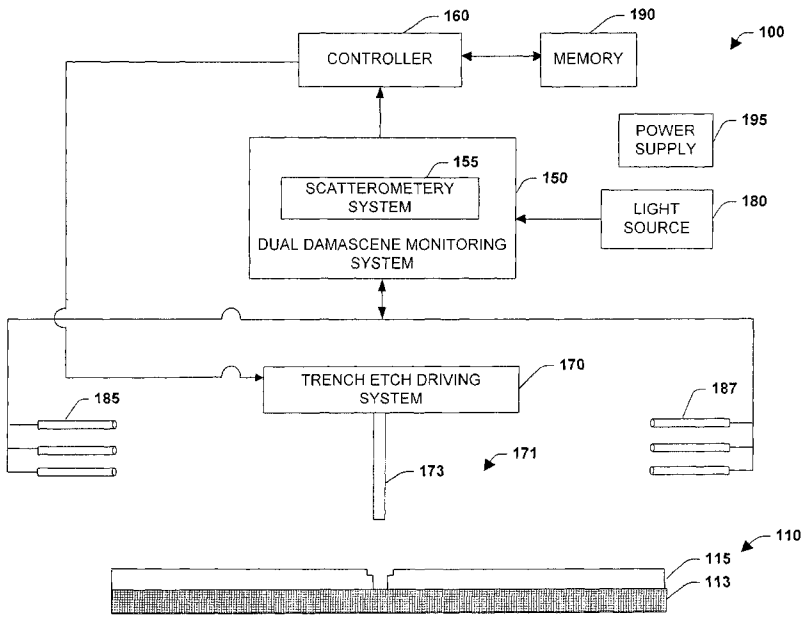
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(54) Title: DUAL DAMASCENE TRENCH DEPTH MONITORING



(57) Abstract: Disclosed are methods of dual damascene processing, involving forming a plurality of via openings in the insulation structure containing a single layer of a dielectric material; and simultaneously (i) forming a plurality of trenches in the insulation structure, each trench positioned along the substantially straight line of a group of via openings, and (ii) monitoring the formation of trenches using a scatterometry system to determine trench depth, and terminating forming the trenches when a desired trench depth is attained.

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